

Yuko Inatomi

List of Publications by Year in descending order

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91
papers

804
citations

643344

15
h-index

799663

21
g-index

92
all docs

92
docs citations

92
times ranked

561
citing authors

#	ARTICLE	IF	CITATIONS
1	Diffusion coefficient analysis method using data statistical processing to reduce interference fringe noise effects. <i>AIChE Journal</i> , 2022, 68, e17497.	1.8	1
2	Natural convection induced by unintended horizontal temperature distribution in a narrow-closed container heated from above. <i>International Journal of Heat and Mass Transfer</i> , 2022, 183, 122018.	2.5	0
3	Numerical Prediction of the Spontaneous Ignition of Cool Flame for the Microgravity Experiment by Using Sounding Rocket. <i>Transactions of the Japan Society for Aeronautical and Space Sciences Aerospace Technology Japan</i> , 2021, 19, 539-544.	0.1	0
4	Numerical investigation of growth interface shape and compositional distributions in SiGe crystals grown by the TLZ method in the International Space Station. <i>Journal of Crystal Growth</i> , 2021, 566-567, 126157.	0.7	0
5	Estimation of the diffusion coefficient of GaSb in InSb melt using Bayesian optimization and the ISS experimental results. <i>Journal of Crystal Growth</i> , 2021, 573, 126280.	0.7	4
6	Enhanced seebeck coefficient and low thermal conductivity of Cu ₂ SexTe _{1-x} solid solutions via minority carrier blocking and interfacial effects. <i>Journal of Alloys and Compounds</i> , 2020, 835, 155188.	2.8	9
7	Study on crystal growth of $\text{In}_{1-x}\text{Ga}_x\text{Sb}$ under microgravity. <i>Scientia Sinica: Physica, Mechanica Et Astronomica</i> , 2020, 50, 047002.		
8	An Approach to Optimize the Thermoelectric Properties of III-V Ternary InGaSb Crystals by Defect Engineering via Point Defects and Microscale Compositional Segregations. <i>Inorganic Chemistry</i> , 2019, 58, 11579-11588.	1.9	9
9	Numerical Investigation of the Effect of Heating Rate on InGaSb Crystal Growth under Zero-Gravity. <i>Microgravity Science and Technology</i> , 2019, 31, 377-380.	0.7	5
10	Analysis Method Using Two-Wavelength Mach-Zehnder Interferometer for the Measurement of Soret Coefficients in Soret-Facet Mission on ISS. <i>Microgravity Science and Technology</i> , 2019, 31, 49-59.	0.7	5
11	Homogeneous InGaSb crystal grown under microgravity using Chinese recovery satellite SJ-10. <i>Npj Microgravity</i> , 2019, 5, 8.	1.9	12
12	Enhanced thermoelectric properties of InSb: Studies on In/Ga doped GaSb/InSb crystals. <i>Intermetallics</i> , 2019, 105, 21-28.	1.8	15
13	Orientation-dependent dissolution and growth kinetics of $\text{In}_x\text{Ga}_{1-x}\text{Sb}$ by vertical gradient freezing method under microgravity. <i>Journal of Crystal Growth</i> , 2018, 496-497, 15-17.	0.7	8
14	Sounding-rocket microgravity experiments on alumina dust. <i>Nature Communications</i> , 2018, 9, 3820.	5.8	13
15	Study of SiGe Crystal Growth Interface Processed in Microgravity. <i>Crystal Growth and Design</i> , 2018, 18, 3697-3703.	1.4	8
16	Pure iron grains are rare in the universe. <i>Science Advances</i> , 2017, 3, e1601992.	4.7	25
17	Crystallization kinetics in Si-1 at%Sn during rapid solidification in undercooled melt. <i>Journal of Crystal Growth</i> , 2017, 468, 73-78.	0.7	5
18	Investigation of directionally solidified InGaSb ternary alloys from Ga and Sb faces of GaSb(111) under prolonged microgravity at the International Space Station. <i>Npj Microgravity</i> , 2016, 2, 16026.	1.9	11

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19	Vertical gradient solution growth of N-type Si _{0.73} Ge _{0.27} bulk crystals with homogeneous composition and its thermoelectric properties. <i>Journal of Crystal Growth</i> , 2016, 442, 102-109.	0.7	3
20	A Review on InGaSb Growth under Microgravity and Terrestrial Conditions Towards Future Crystal Growth Project Using Chinese Recovery Satellite SJ-10. <i>Microgravity Science and Technology</i> , 2016, 28, 143-154.	0.7	6
21	Effects of varying indium composition on the thermoelectric properties of In _x Ga _{1-x} Sb ternary alloys. <i>Applied Physics A: Materials Science and Processing</i> , 2016, 122, 1.	1.1	17
22	Effects of temperature gradient in the growth of Si _{0.5} Ge _{0.5} crystals by the traveling liquidus-zone method on board the International Space Station. <i>Journal of Crystal Growth</i> , 2016, 455, 49-54.	0.7	6
23	Numerical simulation model by volume averaging for the dissolution process of GaSb into InSb in a sandwich system. <i>Numerical Heat Transfer, Part B: Fundamentals</i> , 2016, 70, 441-458.	0.6	11
24	Growth of In _x Ga _{1-x} Sb alloy semiconductor at the International Space Station (ISS) and comparison with terrestrial experiments. <i>Npj Microgravity</i> , 2015, 1, 15011.	1.9	24
25	Viscosity Measurements of Molten In _x Ga _{1-x} Sb toward the Experiment of Semiconductor Crystal Growth on the ISS. <i>Netsu Bussei</i> , 2015, 27, 152-163.	0.1	0
26	An experimental verification of a criterion for forming metastable phases in containerless solidification. <i>Journal of Applied Physics</i> , 2015, 117, .	1.1	9
27	A Numerical Study on the Growth Process of InGaSb Crystals Under Microgravity with Interfacial Kinetics. <i>Microgravity Science and Technology</i> , 2015, 27, 313-320.	0.7	10
28	High Power Factor of Ga-Doped Compositionally Homogeneous Si _{0.68} Ge _{0.32} Bulk Crystal Grown by the Vertical Temperature Gradient Freezing Method. <i>Crystal Growth and Design</i> , 2015, 15, 1380-1388.	1.4	5
29	Compositional uniformity of a Si _{0.5} Ge _{0.5} crystal grown on board the International Space Station. <i>Journal of Crystal Growth</i> , 2015, 419, 47-51.	0.7	9
30	SiGe crystal growth aboard the international space station. <i>Journal of Crystal Growth</i> , 2015, 417, 31-36.	0.7	5
31	Crystal Growth of Ternary Alloy Semiconductor and Preliminary Study for Microgravity Experiment at the International Space Station. <i>Transactions of the Japan Society for Aeronautical and Space Sciences Aerospace Technology Japan</i> , 2014, 12, Ph_31-Ph_35.	0.1	3
32	Analysis of dissolution and growth process of SiGe alloy semiconductor based on penetrated X-ray intensities. <i>Journal of Alloys and Compounds</i> , 2014, 590, 96-101.	2.8	3
33	Thermal properties of molten InSb, GaSb, and In _x Ga _{1-x} Sb alloy semiconductor materials in preparation for crystal growth experiments on the international space station. <i>Advances in Space Research</i> , 2014, 53, 689-695.	1.2	4
34	Viscosity of Molten InSb, GaSb, and In _x Ga _{1-x} Sb Alloy Semiconductors. <i>International Journal of Thermophysics</i> , 2014, 35, 352-360.	1.0	2
35	In-situ observation of faceted growth of benzophenone single crystals. <i>Materials Chemistry and Physics</i> , 2014, 144, 402-408.	2.0	8
36	Growth of a Si _{0.50} Ge _{0.50} crystal by the traveling liquidus-zone (TLZ) method in microgravity. <i>Journal of Crystal Growth</i> , 2014, 388, 12-16.	0.7	19

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37	Numerical simulations of SiGe crystal growth by the traveling liquidus-zone method in a microgravity environment. <i>Journal of Crystal Growth</i> , 2014, 402, 71-77.	0.7	12
38	Simultaneous measurement of temperature and concentration during faceted cellular array growth under microgravity. <i>World Journal of Engineering</i> , 2014, 11, 41-48.	1.0	5
39	Growth of InGaSb Alloy Semiconductor Bulk Crystals under Microgravity. <i>Hyomen Kagaku</i> , 2012, 33, 687-693.	0.0	0
40	Homogeneous SiGe crystal growth in microgravity by the travelling liquidus-zone method. <i>Journal of Physics: Conference Series</i> , 2011, 327, 012017.	0.3	10
41	Growth of homogeneous polycrystalline Si _{1-x} Ge _x and Mg ₂ Si _{1-x} Ge _x for thermoelectric application. <i>Thin Solid Films</i> , 2011, 519, 8532-8537.	0.8	15
42	Effects of solutal convection on the dissolution of GaSb into InSb melt and solute transport mechanism in InGaSb solution: Numerical simulations and in-situ observation experiments. <i>Journal of Crystal Growth</i> , 2011, 324, 157-162.	0.7	14
43	Growth of Si _{1-x} Ge bulk crystals with highly homogeneous composition for thermoelectric applications. <i>Journal of Crystal Growth</i> , 2011, 318, 324-327.	0.7	10
44	Three-dimensional Phase Field Modeling of the Faceted Cellular Growth. <i>ISIJ International</i> , 2010, 50, 1901-1907.	0.6	7
45	In-situ observations of dissolution process of GaSb into InSb melt by X-ray penetration method. <i>Journal of Crystal Growth</i> , 2010, 312, 2677-2682.	0.7	16
46	In situ visualization of crystallization inside high temperature silicate melts. <i>Journal of Applied Physics</i> , 2010, 107, .	1.1	11
47	Real-time optical system for observing crystallization in levitated silicate melt droplets. <i>Review of Scientific Instruments</i> , 2010, 81, 073708.	0.6	3
48	Alloy Semiconductor Crystal Growth Under Microgravity. , 2010, , .		0
49	Uncertainties in crystallization of henâ€œgg white lysozyme: reproducibility issue. <i>Crystal Research and Technology</i> , 2008, 43, 447-454.	0.6	20
50	Interferometry measurement of protein concentration evolution during crystallization and dissolution with improved reliability and versatility. <i>Measurement Science and Technology</i> , 2008, 19, 045303.	1.4	12
51	Convective Behavior Of Low Prandtl Number Fluid Heated On Centrifuge. <i>AIP Conference Proceedings</i> , 2008, , .	0.3	0
52	Density and Thermal Conductivity Measurements for Silicon Melt by Electromagnetic Levitation under a Static Magnetic Field. <i>International Journal of Thermophysics</i> , 2007, 28, 44-59.	1.0	32
53	Influence of Ultrasound on Crystal Growth from Solution and Related Flow Visualization. <i>Crystal Growth and Design</i> , 2006, 6, 2412-2416.	1.4	10
54	Buoyancy convection in cylindrical conducting melt with low Grashof number under uniform static magnetic field. <i>International Journal of Heat and Mass Transfer</i> , 2006, 49, 4821-4830.	2.5	15

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55	Measurements of interdiffusion coefficients in metallic melts at high temperature under horizontal static magnetic field. <i>Microgravity Science and Technology</i> , 2006, 18, 86-90.	0.7	8
56	Time-of-Flight Secondary Mass Spectrometry Analysis of Isotope Composition for Measurement of Self-Diffusion Coefficient. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 5274-5276.	0.8	5
57	In situ observation for semiconductor solution growth using a near-infrared microscope. <i>Journal of Crystal Growth</i> , 2005, 275, 193-200.	0.7	14
58	Growth and structure of CdZnTe crystal from Te solution with THM technique under static magnetic field. <i>Journal of Crystal Growth</i> , 2005, 275, e1551-e1556.	0.7	19
59	Growth interface of CdZnTe grown from Te solution with THM technique under static magnetic field. <i>Journal of Crystal Growth</i> , 2005, 284, 406-411.	0.7	40
60	Determination of butanol distribution on salol-butanol crystals using Micro Raman Spectroscopy. <i>Microgravity Science and Technology</i> , 2005, 16, 104-106.	0.7	0
61	A two-stage technique for single crystal growth of HgCdTe using a pressurized Bridgman method. <i>Journal of Crystal Growth</i> , 2004, 263, 273-282.	0.7	5
62	Growth and properties of 40mm diameter Hg _{1-x} CdxTe using the two-stage Pressurised Bridgman Method. <i>Journal of Crystal Growth</i> , 2004, 273, 54-62.	0.7	1
63	In situ observation experiment for semiconductor solution growth under reduced convection condition – a review. <i>Crystal Research and Technology</i> , 2003, 38, 535-541.	0.6	4
64	Measurement of temperature and concentration dependences of refractive index of hen-egg-white lysozyme solution. <i>Crystal Research and Technology</i> , 2003, 38, 785-792.	0.6	15
65	In situ Observation Experiment for Semiconductor Solution Growth under Reduced Convection Condition – A Review. <i>ChemInform</i> , 2003, 34, no.	0.1	0
66	Strong magnetic field effect on the dissolution process of tetragonal lysozyme crystals. <i>Advances in Space Research</i> , 2003, 32, 217-223.	1.2	6
67	Morphological stability of gap growth interface in LPE under reduced convection condition. , 2002, , .		0
68	Measurement of Diffusion Coefficient in Liquid Metal under Static Magnetic Field. <i>Japanese Journal of Applied Physics</i> , 2002, 41, L811-L813.	0.8	31
69	An investigation of magnetic field effects on the dissolution of lysozyme crystal and related phenomena. <i>Acta Crystallographica Section D: Biological Crystallography</i> , 2002, 58, 2024-2030.	2.5	11
70	Growth kinetics of GaP in LPE. <i>Journal of Crystal Growth</i> , 2002, 237-239, 1428-1433.	0.7	2
71	Morphological stability of GaP(111)B in LPE under static magnetic field. <i>Journal of Crystal Growth</i> , 2002, 241, 395-403.	0.7	11
72	Dissolution Rate of GaP Crystal on a Centrifuge. , 2001, , 83-91.		1

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73	Study of lysozyme crystal growth under a strong magnetic field using a Mach-Zehnder interferometer. Journal of Crystal Growth, 2001, 226, 534-542.	0.7	38
74	Scaling Analysis of Semiconductor Crystal Growth from the Liquid Phase in an Axis Static Magnetic Field. Materials Transactions, JIM, 2000, 41, 1026-1033.	0.9	12
75	Measurement of Refractive Index of GaP Crystal over a Large Temperature Range Using Interferometry. Crystal Research and Technology, 2000, 35, 221-228.	0.6	9
76	Morphological change of semiconductor growth interface from solution in a magnetic field. Journal of Crystal Growth, 1999, 198-199, 176-181.	0.7	3
77	Semiconductor growth interface from solution in short-duration low-gravity environment. , 1999, , .		3
78	Growth and Dissolution Rates on GaP(111)B Facet Surface during Solution Growth under a Transverse Static Magnetic Field. Crystal Research and Technology, 1998, 33, 857-866.	0.6	5
79	In situ Observation Setup for Semiconductor Growth Interface from Solution in a Magnetic Field. Crystal Research and Technology, 1997, 32, 759-768.	0.6	9
80	Directional Solidification of Faceting Material in a Centrifuge. Crystal Research and Technology, 1997, 32, 947-954.	0.6	1
81	Initial transient solute redistribution during directional solidification with liquid flow. Journal of Crystal Growth, 1997, 182, 212-218.	0.7	17
82	In Situ Observation of Directional Solidification in High Gravity. , 1997, , 93-108.		0
83	Influence of Release and Transport of Latent Heat on Solidification Behavior in Faceted Crystal. Materials Science Forum, 1996, 215-216, 339-346.	0.3	2
84	IN SITU OBSERVATION OF FACETED CELLULAR ARRAY GROWTH IN TRANSPARENT ORGANIC MATERIAL. , 1994, , 637-641.		2
85	In-situ observation of unidirectional solidification in transparent organic alloy. Journal of Crystal Growth, 1993, 128, 178-182.	0.7	9
86	In-situ observation of morphological change on LPE grown surface in semiconductors. Journal of Crystal Growth, 1993, 128, 557-561.	0.7	8
87	Influence of mixing in liquid on unidirectional solidification rate in transparent organic alloy. Journal of Crystal Growth, 1993, 130, 85-95.	0.7	12
88	Real-time measurement of LPE growth rate in GaP. Journal of Crystal Growth, 1991, 114, 380-388.	0.7	13
89	Direct observation of LPE growth in GaP. Journal of Crystal Growth, 1990, 99, 124-127.	0.7	11
90	Bulk Growth of InGaSb Alloy Semiconductor under Terrestrial Conditions: A Preliminary Study for Microgravity Experiments at ISS. Defect and Diffusion Forum, 0, 323-325, 539-544.	0.4	8

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91	Investigation on Mechanism of Faceted Cellular Array Growth in International Space Station. Defect and Diffusion Forum, 0, 323-325, 533-537.	0.4	2